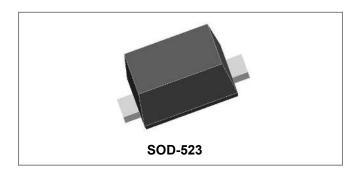


CESD3V3D5 THRU CESD24VD5

Technical Data Data Sheet N1872, Rev. C

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# CESD3V3D5 THRU CESD24VD5 ESD Protection Diodes



# **Schematic & Pin Configuration**



### Description

The CESD3V3D5 THRU CESD24VD5 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

### **Mechanical Data**

- Stand-off Voltage: 3.3 V-24V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3B per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices

### Maximum Ratings @T<sub>A</sub>=25° C unless otherwise specified

Parameter	Symbol	Value	Units
ESD per IEC 61000-4-2 (Air)	V <sub>ESD</sub>	±25	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±25	
Peak Pulse Power (Note 1)	P <sub>PP</sub>	210(CESD3V3D5) 170(CESD5V0D5) 220(CESD12VD5) 323(CESD15VD5) 330(CESD24VD5)	W
Thermal Resistance Junction-to-Ambient R <sub>θJ</sub>		833	°C/W
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C
Operating Junction Temperature Range	TJ	-55 to + 150	°C
Storage Temperature Range		-55 to + 150	°C

Note1. Non-repetitive current pulse 8/20µs exponential decay waveform according to IEC61000-4-5.

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### **Electrical Characteristics@25°C**

Symbol	Parameter			
IPP	Maximum Reverse Peak Pulse Current			
Vc	Clamping Voltage @ IPP			
V <sub>RWM</sub>	Working Peak Reverse Voltage			
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>			
V <sub>BR</sub>	Breakdown Voltage @ I⊤			
I <sub>T</sub>	Test Current			
I <sub>F</sub>	Forward Current			
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>			
С	Max. Capacitance $@V_R=0$ and f =1MHz			

Device*	Device Marking	V <sub>RWM</sub> (V)	I <sub>R</sub> (µА) @V <sub>RWM</sub>	V <sub>BR</sub> (V) @ I <sub>T</sub> (Note 2)		Ιτ	lpp (A)*	Vc(V) @Max Ipp*	C(pF)
		Max.	Max.	Min.	Max.	mA	Max.	Max.	Тур.
CESD3V3D5	ZE	3.3	1	5.0	5.9	1.0	16	13	120
CESD5V0D5	ZF	5.0	10	6.2	7.3	1.0	13	13	95
CESD12VD5	ZM	12	1	14.1	16.5	1.0	9	24	45
CESD15VD5	ZP	15	1	16.7	20	1.0	9.5	34	48
CESD24VD5	ZY	24	1	26.7	33	1.0	7.5	44	36

\*Other voltages available upon request.

2. VBR is measured with a pulse test current I⊤ at an ambient temperature of 25°C.

### **Ratings and Characteristics Curves**

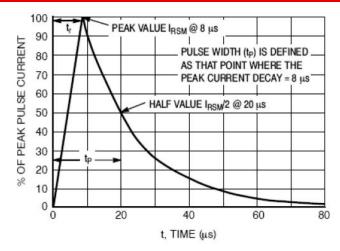


Figure 1. 8 x 20 µs Pulse Waveform

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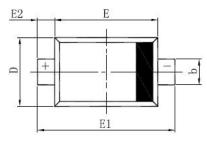
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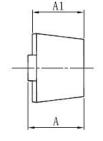
## **Ordering Information**

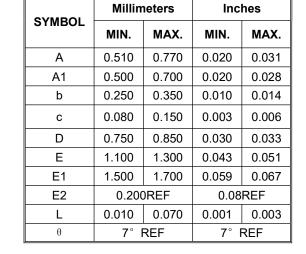
Device	Package	Shipping	
CESD Series	SOD-523 (Pb-Free)	8000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Mechanical Dimensions SOD-523**

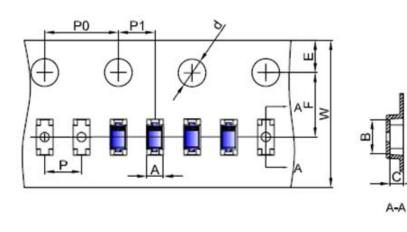






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### **Carrier Tape Specification SOD-523**

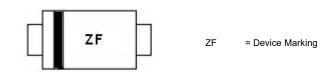


	SYMBOL	Millimeters				
	STWDUL	Min.	Max.			
	A	0.85	0.95			
	В	1.89	1.99			
	С	0.68	0.78			
	d	1.40	1.60			
	E	1.65	1.85			
	F	3.40	3.60			
-	Р	1.90	2.10			
	P0	3.90	4.10			
	P1	1.90	2.10			
	W	7.90	8.30			

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# Marking Diagram



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